NPN-Silizium-Fototransistor im SMT SIDELED®-Gehäuse
Silicon NPN Phototransistor in SMT SIDELED®-Package

SFH 325
SFH 325 FA



SFH 325



SFH 325 FA

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 380 nm bis 1150 nm (SFH 325) und bei 880 nm (SFH 325 FA)
- Hohe Linearität
- P-LCC-2 Gehäuse
- Gruppiert lieferbar
- Nur für Reflow IR-Lötung geeignet.

Anwendungen

- Miniaturlichtschranken für Gleich- und Wechsellichtbetrieb
- Lochstreifenleser
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 380 nm to 1150 nm (SFH 325) and of 880 nm (SFH 325 FA)
- High linearity
- P-LCC-2 package
- Available in groups
- Suitable only for reflow IR soldering.

Applications

- Miniature photointerrupters
- Punched tape readers
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code	Typ Type	Bestellnummer Ordering Code
SFH 325	Q6[1)]2702-P1638	SFH 325 FA	Q62702-P1639
SFH 325-3	Q62702-P1610	SFH 325 FA-3	Q62702-P1724
SFH 325-3/-4	Q62702-P3604	SFH 325 FA-3/-4	Q62702-P3603
SFH 325-4	Q62702-P1611	SFH 325 FA-4	Q62702-P1615

1)

Grenzwerte
Maximum Ratings

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}; T_{stg}	– 40 … + 100	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	35	V
Kollektorstrom Collector current	I_C	15	mA
Kollektorspitzenstrom, $\tau < 10\ \mu s$ Collector surge current	I_{CS}	75	mA
Verlustleistung, T_A = 25 °C Total power dissipation	P_{tot}	165	mW
Wärmewiderstand für Montage auf PC-Board Thermal resistance for mounting on pcb	R_{thJA}	450	K/W

Kennwerte (T_A = 25 °C, λ = 950 nm)
Characteristics

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		SFH 325	**SFH 325 FA**	
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	860	900	nm
Spektraler Bereich der Fotoempfindlichkeit S = 10% von S_{max} Spectral range of sensitivity S = 10% of S_{max}	λ	380 … 1150	730 … 1120	nm
Bestrahlungsempfindliche Fläche (∅ 220 µm) Radiant sensitive area	A	0.038	0.038	mm^2
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	0.45 × 0.45	0.45 × 0.45	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	0.5 … 0.7	0.5 … 0.7	mm
Halbwinkel Half angle	φ	± 60	± 60	Grad deg.
Kapazität, V_{CE} = 0 V, f = 1 MHz, E = 0 Capacitance	C_{CE}	5.0	5.0	pF
Dunkelstrom Dark current V_{CE} = 25 V, E = 0	I_{CEO}	1 (≤ 200)	1 (≤ 200)	nA

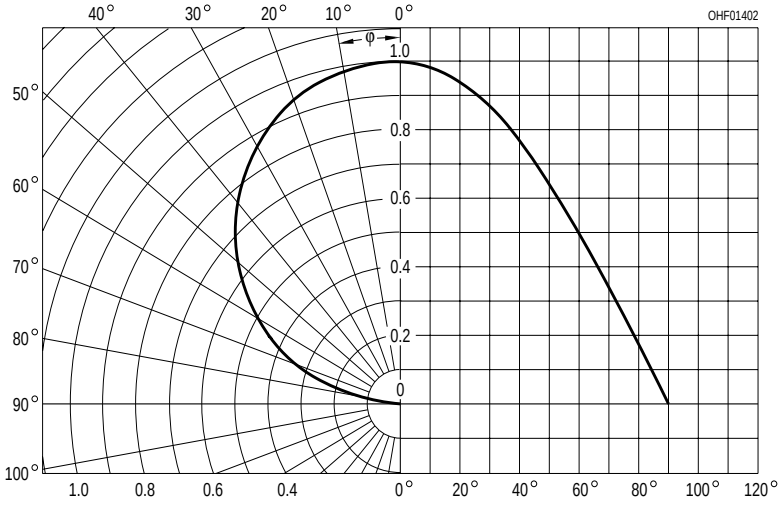
Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.
The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**				**Einheit** **Unit**
		SFH 325 /FA	**-2**	**-3**	**-4**	
Fotostrom, $\lambda = 950$ nm Photocurrent E_e = 0.1 mW/cm², V_{CE} = 5 V	I_{PCE}	≥ 16	16 … 32	25 … 50	40 … 80	µA
SFH 325: E_v = 1000 lx, Normlicht/standard light A, V_{CE} = 5 V	I_{PCE}	–	420	650	1000	µA
Anstiegszeit/Abfallzeit Rise and fall time I_C = 1 mA, V_{CC} = 5 V, R_L = 1 kΩ	t_r, t_f	7	6	7	8	µs
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}$[1] × 0.3, E_e = 0.1 mW/cm²	V_{CEsat}	150	150	150	150	mV

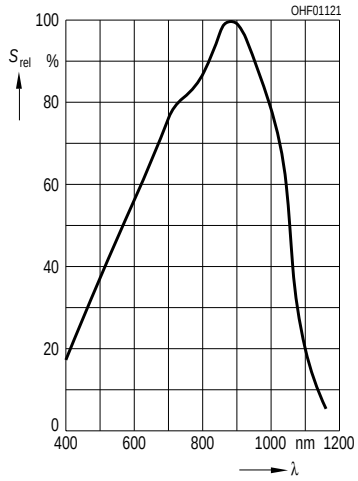
[1] I_{PCEmin} ist der minimale Fotostrom der jeweiligen Gruppe.

[1] I_{PCEmin} is the min. photocurrent of the specified group.

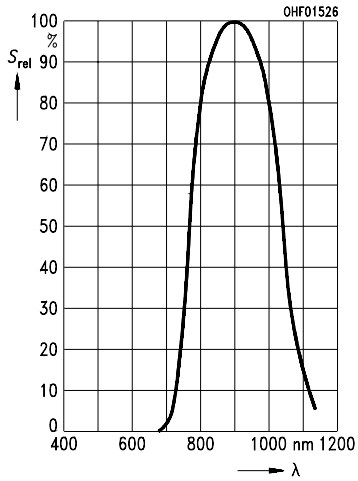
Directional Characteristics $S_{rel} = f(\varphi)$



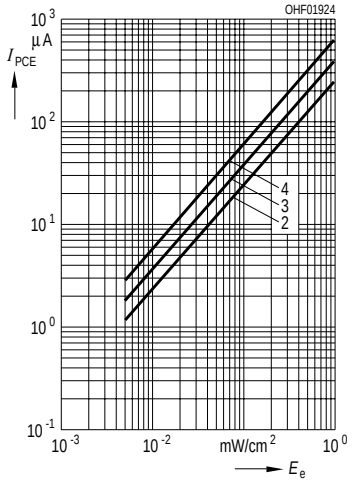
Relative Spectral Sensitivity,
SFH 325 $S_{rel} = f(\lambda)$



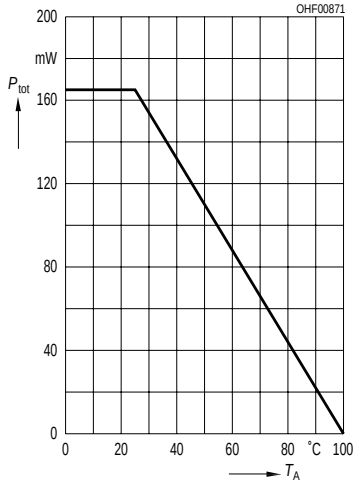
Relative Spectral Sensitivity,
SFH 325 FA $S_{rel} = f(\lambda)$



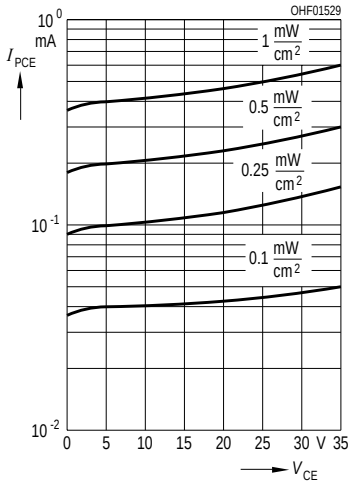
Photocurrent
$I_{PCE} = f(E_e)$, V_{CE} = 5 V



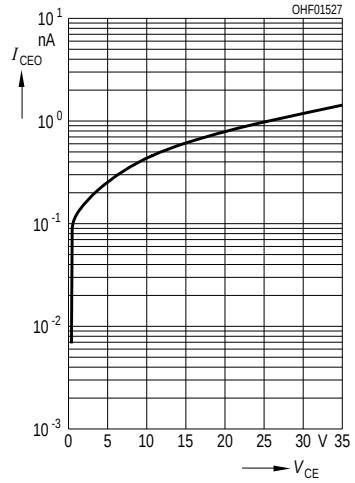
Total Power Dissipation
$P_{tot} = f(T_A)$



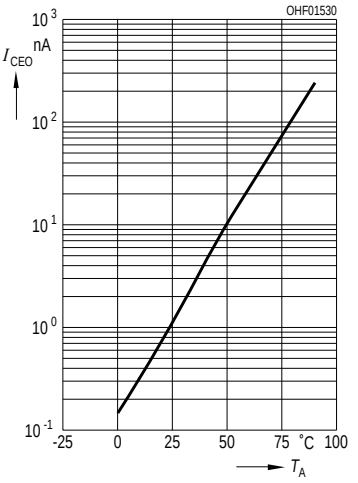
Photocurrent
$I_{PCE} = f(V_{CE})$, E_e = Parameter



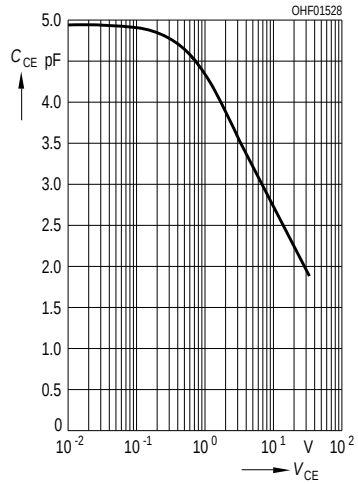
Dark Current
$I_{CEO} = f(V_{CE})$, E = 0



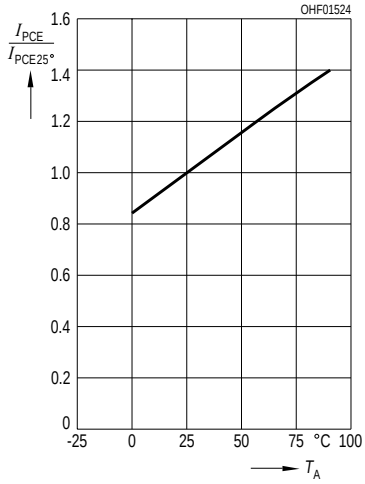
Dark Current
$I_{CEO} = f(T_A)$, V_{CE} = 5 V, E = 0



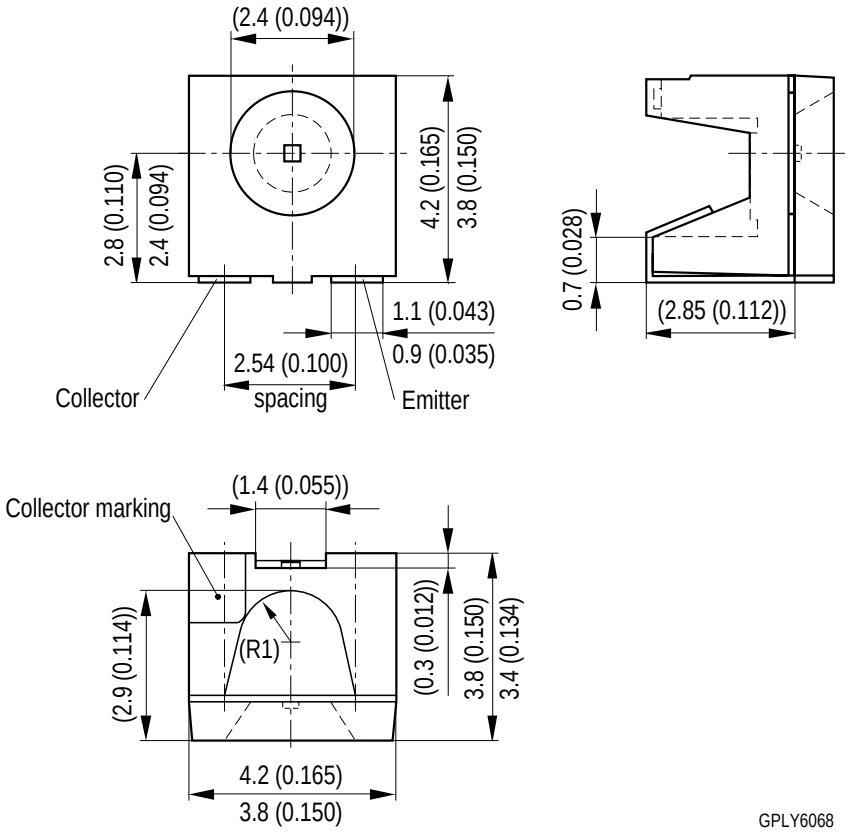
Capacitance
$C_{CE} = f(V_{CE})$, f = 1 MHz, E = 0



Photocurrent
$I_{PCE}/I_{PCE25°} = f(T_A)$, V_{CE} = 5 V



Maßzeichnung
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Löthinweise
Soldering Conditions

Bauform Types	Tauch-, Schwall- und Schlepplötung Dip, Wave and Drag Soldering			Reflowlötung Reflow Soldering	
	Lötbad-temperatur Temperature of the Soldering Bath	Maximal zulässige Lötzeit Max. Perm. Soldering Time	Abstand Lötstelle – Gehäuse Distance between Solder Joint and Case	Lötzonen-temperatur Temperature of Soldering Zone	Maximale Durchlaufzeit Max. Transit Time
SIDELED	–	–	–	245 °C	10 s

Zusätzliche Informationen über allgemeine Lötbedingungen erhalten Sie auf Anfrage.

For additional information on general soldering conditions please contact us.

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Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9